

VN3205N3-G Information



For Reference Only

Part Number VN3205N3-G

Manufacturer Microchip Technology

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 50V 1.2A TO92-3

Package TO-226-3, TO-92-3 (TO-226AA)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

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VN3205N3-G Specifications

Manufacturer Part Number VN3205N3-G Manufacturer Microchip Technology Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-226-3, TO-92-3 (TO-226AA) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 50V Current - Continuous Drain (Id) @ 25°C 1.2A (Tj) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.4V @ 10mA Gate Charge (Qg) (Max) @ Vgs 300pF @ 25V Vgs (Max) ± 20V FET Feature - Power Dissipation (Max) 1W (Tc) Rds On (Max) @ Id, Vgs 300 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-226-3, TO-92-3 (TO-226AA) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 50V Current - Continuous Drain (Id) @ 25°C 1.2A (Tj) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.4V @ 10mA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 300pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1W (Tc) Rds On (Max) @ Id, Vgs 300 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Manufacturer Part Number	VN3205N3-G
Package To-226-3, To-92-3 (To-226AA) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 50V Current - Continuous Drain (Id) @ 25°C 1.2A (Tj) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.4V @ 10mA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 300pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1W (Tc) Rds On (Max) @ Id, Vgs 300 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Manufacturer	Microchip Technology
Package TO-226-3, TO-92-3 (TO-226AA) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 50V Current - Continuous Drain (Id) @ 25°C 1.2A (Tj) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.4V @ 10mA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 300pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) IW (Tc) Rds On (Max) @ Id, Vgs 300 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Category	Discrete Semiconductor Products
Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 50V Current - Continuous Drain (Id) @ 25°C 1.2A (Tj) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.4V @ 10mA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 300pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1W (Tc) Rds On (Max) @ Id, Vgs 300 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 (TO-226AA)		Transistors - FETs, MOSFETs - Single
FET Type Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Supplier Device Package Package / Case N-Channel MOSFET (Metal Oxide) MOSFET (Metal Oxide) MOSFET (Metal Oxide) 1.2A (Tj) 1	Package	TO-226-3, TO-92-3 (TO-226AA)
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 1.2A (Tj) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Jenuth (Vgs) MOSFET (Metal Oxide) 50V 1.2A (Tj) 4.5V, 10V 2.4V @ 10mA 300pF @ 25V 4.5V (10V 300pF @ 25V 4.5V (10V 4.5V (10V 300pF @ 25V 4.5V (10V 4.5V (Series	-
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 1.2A (Tj) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 50V 1.2A (Tj) 3.0V 2.4V @ 10mA 3.00mA 4.5V, 10V 2.4V @ 10mA 3.00mF @ 25V 4.5V 4.5	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature John Charge (Qg) (Max) @ Vds Through Hole Supplier Device Package TO-226-3, TO-92-3 (TO-226AA)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature John Charge (Time Package TO-92-3 TO-226-3, TO-92-3 (TO-226AA)	Drain to Source Voltage (Vdss)	50V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature John Capacitance Through Hole Supplier Device Package TO-92-3 TO-92-3 (TO-226AA)	Current - Continuous Drain (Id) @ 25°C	1.2A (Tj)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature June 100	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Through Hole Supplier Device Package Package / Case 300 pF @ 25V 300 w 300 m Through Hole Through Hole TO-92-3 TO-226-3, TO-92-3 (TO-226AA)	Vgs(th) (Max) @ Id	2.4V @ 10mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1W (Tc)Rds On (Max) @ Id, Vgs300 mOhm @ 3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	Gate Charge (Qg) (Max) @ Vgs	-
FET Feature - Power Dissipation (Max) 1W (Tc) Rds On (Max) @ Id, Vgs 300 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Input Capacitance (Ciss) (Max) @ Vds	300pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs300 mOhm @ 3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Power Dissipation (Max)	1W (Tc)
Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Rds On (Max) @ Id, Vgs	300 mOhm @ 3A, 10V
Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-226-3, TO-92-3 (TO-226AA)	Mounting Type	Through Hole
	Supplier Device Package	TO-92-3
Report errors?	Package / Case	TO-226-3, TO-92-3 (TO-226AA)
		Report errors?

VN3205N3-G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

VN3205N3-G Payment Methods



















VN3205N3-G Shipping Methods













If you have any question about VN3205N3-G, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com